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SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449	26615 PATENT TRADEMARK OFFICE	ATTORNEY'S DKT NO. H1132	APPLICATION NO. ~~Unassigned~~ 10/614,051
		APPLICANT(S) Ming-Ren Lin et al.	
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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

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EXAMINER	DATE CONSIDERED
	9/11/2004

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